

ABSTRACT

In a first aspect, the present invention provides a silicon thin film transistor which comprises:

- a substrate;
- a barrier layer of porous silica (SiO_2) deposited directly on the substrate; and
- a thin layer of silicon that has been caused to be polycrystalline deposited directly on the barrier layer.

The invention also provides a method of manufacturing such a transistor, a display screen including such a transistor, and a method of manufacturing such a display screen.